

Abstract of the Disclosure:

In a method for fabricating a buried bit line for a semiconductor memory, the buried bit line is produced as a diffusion region using a dopant source including polysilicon that has previously been applied above the region intended for the buried bit line. This keeps the extent of diffusion within limits and means that the doped polysilicon is particularly suitable for the formation of the insulating oxide region above the buried bit line, due to the rapid oxidation.

LDP/nt